

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	21	(cathode same (potential adj barrier) same (semiconductor near4 thickness ".clm.near3" nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/22 14:40
L2	1	(cathode same (potential adj barrier) same (semiconductor near4 thickness near3 nm))".clm"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/22 14:41
L3	1	(cathode same (potential adj barrier) same (semiconductor near4 thickness near3 nm))".clm"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/22 14:41
L4	1	(cathode same (potential adj barrier) same (semiconductor near4 thickness near3 nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/22 14:42
L5	0	(cathode same (potential adj barrier adj3 height) same (semiconductor near4 thickness near3 nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/22 14:42
L6	0	("5721467").URPN.	USPAT	OR	ON	2006/01/22 14:42
L7	3	("5308439" "5384509" "5610471").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/22 14:49